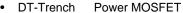
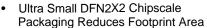


P-Channel 150-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
- 150	2.1 at V _{GS} = - 10 V	- 1.7			

FEATURES



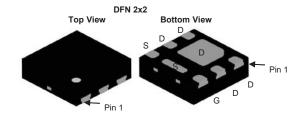


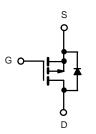


ROHS

APPLICATIONS

- · Active Clamp Circuits in DC/DC Power Supplies
- Load switch





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	LIMIT			
Drain-Source Voltage		V _{DS}	- 150	V		
Gate-Source Voltage		V _{GS}	± 20	- V		
Continuous Drain Current (T _{.I} = 150 °C) ^{a, b}	T _A = 25 °C		- 1.7			
Continuous Drain Current (1 _J = 150 °C) ^{s, s}	T _A = 70 °C	l I _D	- 1.5			
Pulsed Drain Current		I _{DM}	- 6.5	А		
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	- 1.7			
Single Pulse Avalanche Current	L = 1.0 mH	I _{AS}	-1.5			
Single Pulse Avalanche Energy	L = 1.0 IIII	E _{AS}	0.12	mJ		
Mariana Barra Birata ya a h	T _C = 25 °C	P _D	16.2	W		
Maximum Power Dissipation ^{a, b}	T _C = 70 °C] 'D =	10.8	vv		
Operating Junction and Storage Temperature Rar	nge	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 5 s	- R _{thJA}	30	50		
	Steady State		60	96	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	8	12]	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.

Rev. 1.0 1





				Limits		i	
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 150			٧	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 2.0		- 4.0		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Cata Valtaga Drain Current	lass	V _{DS} = - 150 V, V _{GS} = 0 V V _{DS} = - 150 V, V _{GS} = 0 V, T _J = 55 °C			- 1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}				- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -15 \text{ V}, V_{GS} = 10 \text{ V}$	- 0.9			Α	
	Б	V _{GS} = - 10 V, I _D = - 0.5 A		2.1	2.7	Ω	
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = - 6 V, I _D = - 0.5 A		2.2	3		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 0.5 A		1.7		S	
Diode Forward Voltage	V_{SD}	I _S = - 0.5 A, V _{GS} = 0 V		- 0.7	- 1.2	٧	
Dynamic ^b							
Total Gate Charge	Qg	V 75 V V 40 V		4.7	10	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -75 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} \cong -0.5 \text{ A}$		1.0			
Gate-Drain Charge	Q _{gd}	ID = - 0.5 A		1.5			
Gate Resistance	R _g	f = 1.0 MHz		9		Ω	
Input Capacitance	C _{iss}			183		pF	
Output Capacitance	C _{oss}	V _{DS} = - 75 V, V _{GS} = 0 V, f = 1 MHz		10			
Reverse Transfer Capacitance	C _{rss}			6			
Switching ^c	•						
-	t _{d(on)}			7	13		
Turn-On Time	t _r	$V_{DD} = -75 \text{ V}, R_L = 75 \Omega$		21	57	ns	
T 0" T'	t _{d(off)}	$I_D \cong -1.0 \text{ A}, V_{GEN} = -10 \text{ V}$ $R_\alpha = 6 \Omega$		10	25		
Turn-Off Time	t _f	1 · · g = 0 · 3 · 2		31	47		
Drain-Source Body Diode Characteristic	s				'		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 1.7	A	
Pulse Diode Forward Current	I _{SM}				- 6.5	ı	
Body Diode Voltage	V_{SD}	I _S = - 0.5 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			49		ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = - 1 A, dI/dt = 100 A/μs, T _{.I} = 25 °C		70		nC	
Reverse Recovery Fall Time	t _a			33			
Reverse Recovery Rise Time	t _b	7		20		ns	

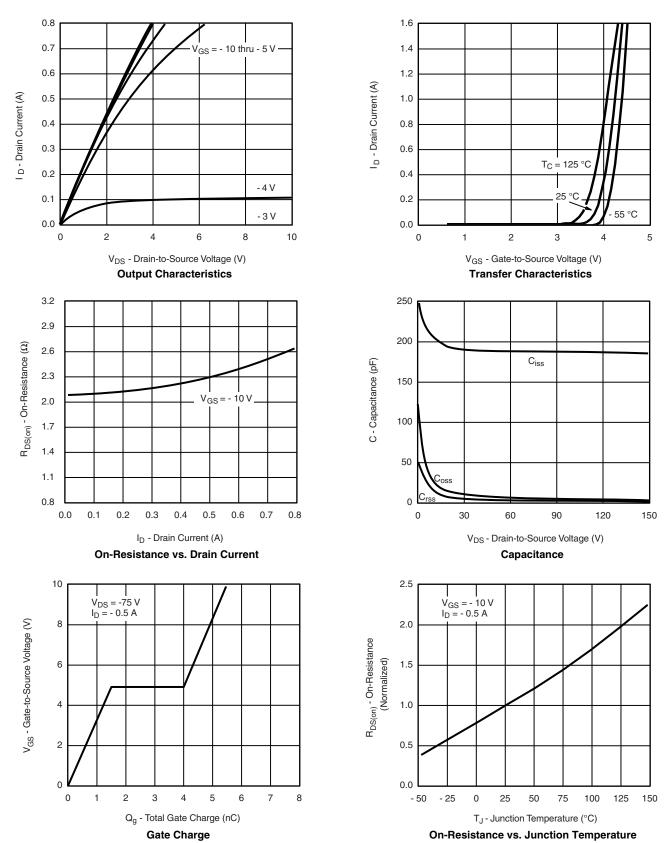
Notes:

- a. Pulse test: PW $\leq 300~\mu s$ duty cycle $\leq 2~\%.$
- b. For DESIGN AID ONLY, not subject to production testing.c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



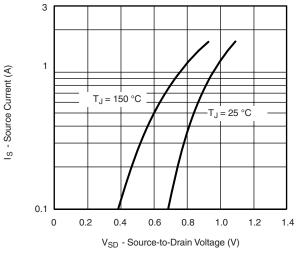
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



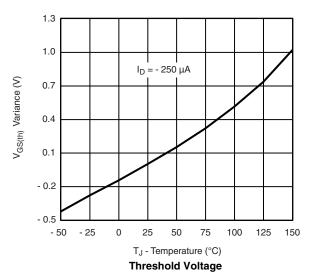




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



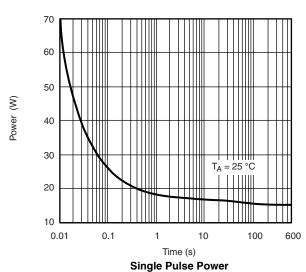
Source-Drain Diode Forward Voltage

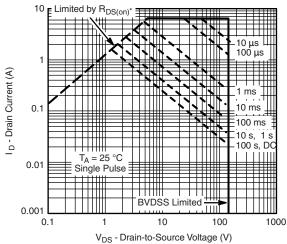


3.0 2.5 2.5 3.0 2.5 2.5 2.5 1.5 1.0 0 2 4 6 8 10

V_{GS} - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage



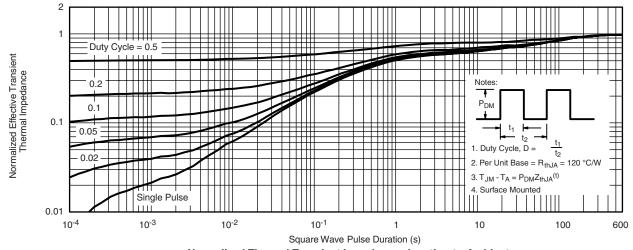


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



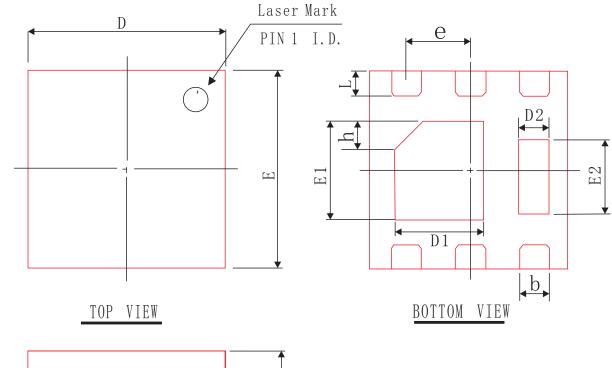
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

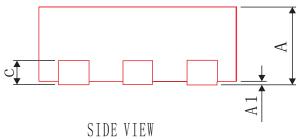


Normalized Thermal Transient Impedance, Junction-to-Ambient



DFN2x2-6L PACKAGE OUTLINE





COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX		
A	0.70	0.75	0.80		
A 1	0.00	0.02	0.05		
b	0.20	0.25	0.30		
D	1.95	2.00	2.07		
Е	1.95	2.00	2.07		
D1	0.80	0.90	1.00		
E1	0.90	1.00	1.10		
D2	0.20	0.30	0.40		
E2	0.65	0.75	0.85		
L	0.20	0.25	0.35		
h	0.20	0.25	0.30		
С	0.203 REF				
е	0 65 BSC				
A*	0.55	0.60	0.65		
A*	0.50	0.55	0.60		

A*: Other thicknesses





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